

isc Silicon PNP Darlington Power Transistor

2SA1046

DESCRIPTION

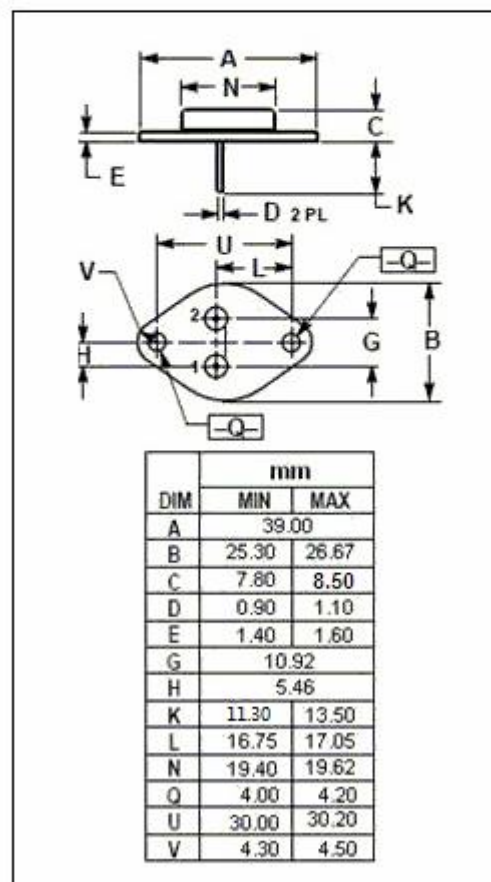
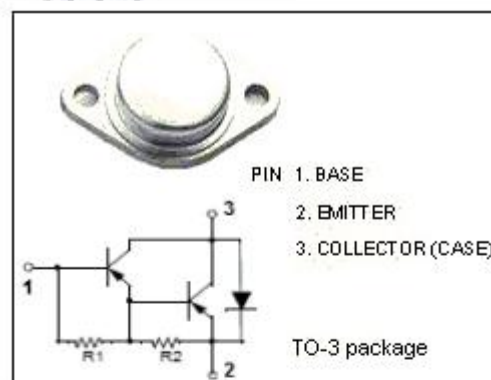
- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -100V(\text{Min})$
- High Current Capability
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power switching applications
- High frequency power amplifier
- DC-DC converters

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	W
T_J	Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~175	$^\circ\text{C}$



isc Silicon PNP Darlington Power Transistor**2SA1046****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; R _{BE} = ∞	-100			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μ A; I _E = 0	-100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -2mA; I _C = 0	-5			V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-50	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-50	μ A
h _{FE}	DC Current Gain	I _C = -3A; V _{CE} = -3V		3000		